DATA SHEET



MOS FIELD EFFECT TRANSISTOR

NP84N055CLE,NP84N055DLE,NP84N055ELE,NP84N055KLE

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

These products are N-channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

- Channel temperature 175 degree rated
- Super low on-state resistance $R_{DS(on)1} = 7.0 \text{ m}\Omega$ MAX. (Vgs = 10 V, ID = 42 A) $R_{DS(on)2} = 8.7 \text{ m}\Omega$ MAX. (Vgs = 5 V, ID = 42 A)
- Low Ciss : Ciss = 6130 pF TYP.
- Built-in gate protection diode

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs = 0 V)	VDSS	55	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±20	V
Drain Current (DC) (Tc = 25°C) ^{Note1}	D(DC)	±84	Α
Drain Current (pulse) Note2	D(pulse)	±336	Α
Total Power Dissipation ($T_A = 25^{\circ}C$)	Рт	1.8	W
Total Power Dissipation (Tc = 25°C)	Рт	200	W
Channel Temperature	Tch	175	°C
Storage Temperature	Tstg	–55 to +175	°C
Single Avalanche Current Note3	AS	84 / 55 / 20	А
Single Avalanche Energy Note3	Eas	70 / 302 / 400	mJ

Notes 1. Calculated constant current according to MAX. allowable channel temperature.

- **2.** PW \leq 10 μ s, Duty cycle \leq 1%
- 3. Starting T_ch = 25°C, V_DD = 28 V, R_G = 25 Ω , V_Gs = 20 \rightarrow 0 V (See Figure 4.)

NP84N055CLE TO-220AB NP84N055DLE TO-262

ORDERING INFORMATION

PART NUMBER

	NP84N055DLE	10-262
	NP84N055ELE	TO-263 (MP-25ZJ)
*	NP84N055KLE	TO-263 (MP-25ZK)



PACKAGE

(TO-220AB)

THERMAL RESISTANCE

Channel to Case Thermal Resistance	Rth(ch-C)	0.75	°C/W
Channel to Ambient Thermal Resistance	Rth(ch-A)	83.3	°C/W

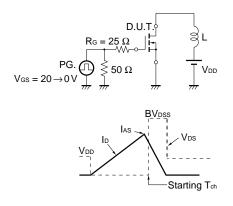
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The mark \star shows major revised points.

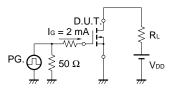
ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	loss	$V_{DS} = 55 V, V_{GS} = 0 V$			10	μA
Gate Leakage Current	lgss	$V_{GS} = \pm 20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$			±10	μΑ
Gate to Source Threshold Voltage	VGS(th)	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	1.5	2.0	2.5	V
Forward Transfer Admittance	yfs	Vds = 10 V, Id = 42 A	27	58		S
Drain to Source On-state Resistance	RDS(on)1	Vgs = 10 V, Id = 42 A		5.6	7.0	mΩ
	RDS(on)2	Vgs = 5 V, Id = 42 A		6.5	8.7	mΩ
	RDS(on)3	Vgs = 4.5 V, Id = 42 A		7.0	9.4	mΩ
Input Capacitance	Ciss	V _{DS} = 25 V		6130	9200	pF
Output Capacitance	Coss	V _{GS} = 0 V		710	1070	pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		350	630	pF
Turn-on Delay Time	td(on)	Vdd = 28 V, Id = 42 A		29	64	ns
Rise Time	tr	V _{GS} = 10 V		19	47	ns
Turn-off Delay Time	$t_{d(off)}$	R _G = 1 Ω		120	230	ns
Fall Time	tr			21	53	ns
Total Gate Charge 1	Q _{G1}	$V_{DD} = 44 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ Id} = 84 \text{ A}$		120	180	nC
Total Gate Charge 2	Q _{G2}	$V_{DD} = 44 V$		65	98	nC
Gate to Source Charge	QGS	V _{GS} = 5 V		18		nC
Gate to Drain Charge	Qgd	ID = 84 A		33		nC
Body Diode Forward Voltage	VF(S-D)	IF = 84 A, VGS = 0 V		1.0		V
Reverse Recovery Time	trr	IF = 84 A, VGS = 0 V		49		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/µs		78		nC

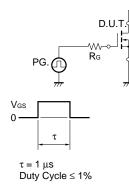
TEST CIRCUIT 1 AVALANCHE CAPABILITY

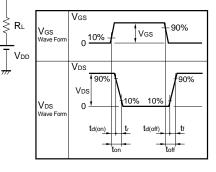


TEST CIRCUIT 3 GATE CHARGE

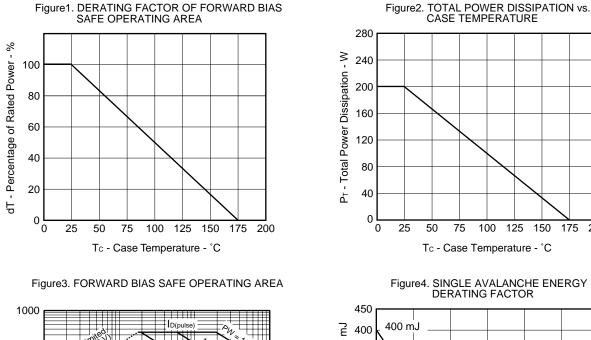


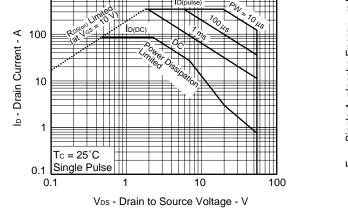
TEST CIRCUIT 2 SWITCHING TIME





TYPICAL CHARACTERISTICS ($T_A = 25^{\circ}C$)





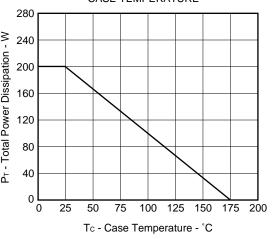
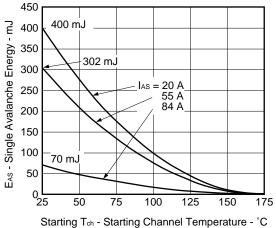


Figure4. SINGLE AVALANCHE ENERGY DERATING FACTOR



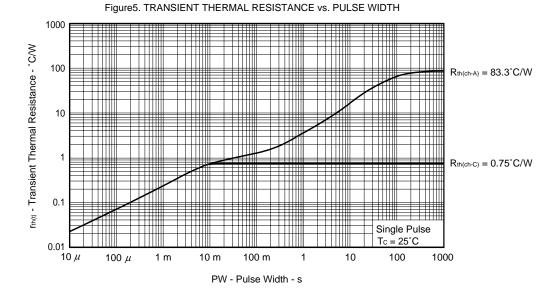
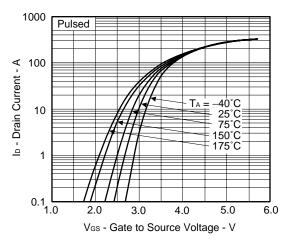
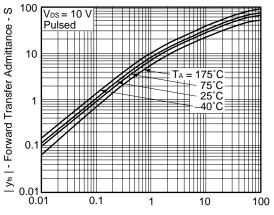
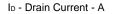


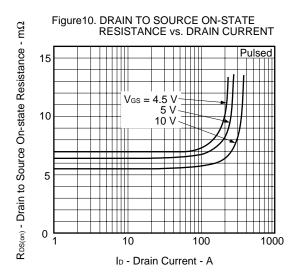
Figure6. FORWARD TRANSFER CHARACTERISTICS











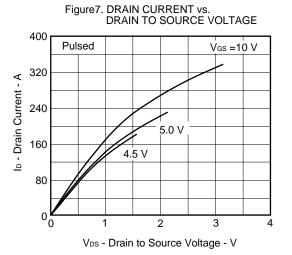


Figure9. DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

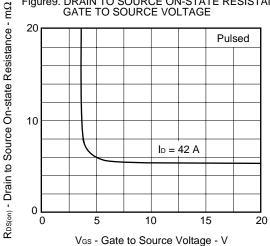
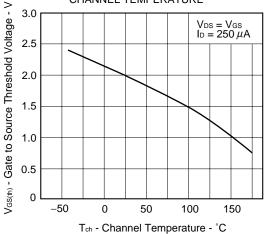
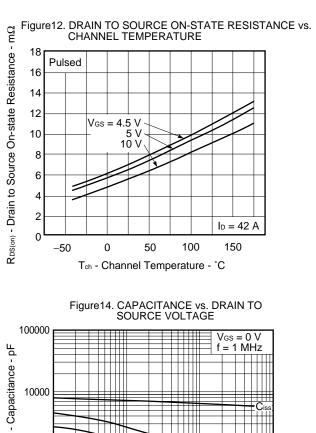
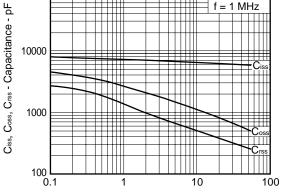


Figure11. GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE



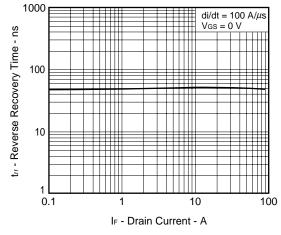


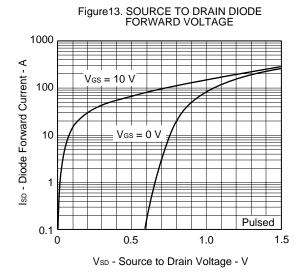
NEC



VDS - Drain to Source Voltage - V







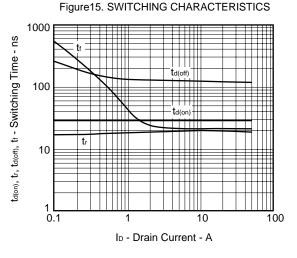
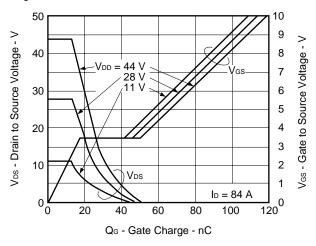


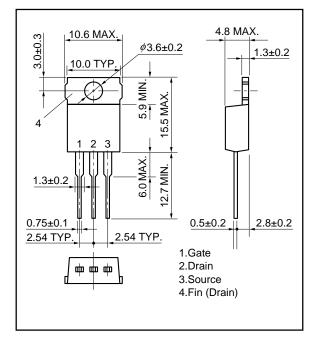
Figure17. DYNAMIC INPUT/OUTPUT CHARACTERISTICS

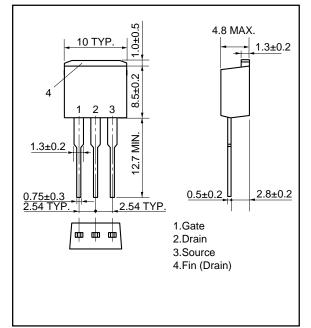


2) TO-262 (MP-25 Fin Cut)

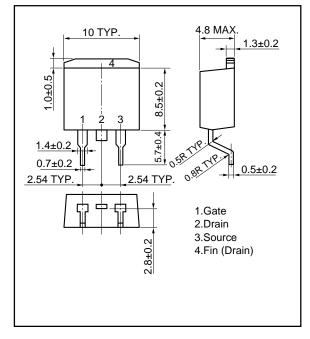
PACKAGE DRAWINGS (Unit: mm)

1) TO-220AB (MP-25)

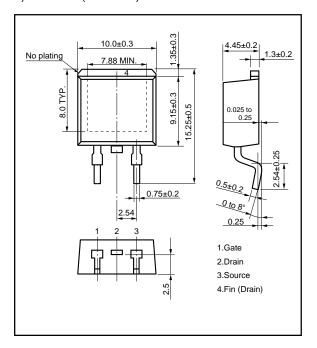




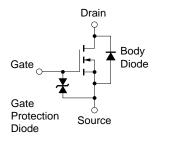
3) TO-263 (MP-25ZJ)



★ 4) TO-263 (MP-25ZK)



EQUIVALENT CIRCUIT



Remark

The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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